

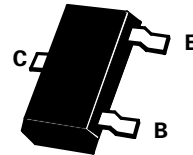
**SOT23 NPN SILICON PLANAR  
MEDIUM POWER TRANSISTOR**

**BCW66**

**ISSUE 4 - MARCH 2001**

PARTMARKING DETAILS –

BCW66F –	EF	BCW66FR –	7P
BCW66G –	EG	BCW66GR –	5T
BCW66H –	EH	BCW66HR –	7M



**SOT23**

COMPLEMENTARY TYPE – BCW68

**ABSOLUTE MAXIMUM RATINGS.**

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	75	V
Collector-Emitter Voltage	$V_{CEO}$	45	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Continuous Collector Current	$I_C$	800	mA
Peak Collector Current(10ms)	$I_{CM}$	1000	mA
Base Current	$I_B$	100	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	330	mW
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 to +150	$^{\circ}C$

# BCW66

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	45			V	$I_{CEO}=10\text{mA}$
	$V_{(BR)CES}$	75			V	$I_C=10\mu\text{A}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_{EBO}=10\mu\text{A}$
Collector-Emitter Cut-off Current	$I_{CES}$			20 20	nA $\mu\text{A}$	$V_{CES} = 45\text{V}$ $V_{CES} = 45\text{V}, T_{amb}=150^{\circ}\text{C}$
Emitter-Base Cut-Off Current	$I_{EBO}$			20	nA	$V_{EBO} = 4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.3 0.7	V V	$I_C=100\text{mA}, I_B = 10\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			2	V	$I_C=500\text{mA}, I_B=50\text{mA}^*$
Static Forward Current Transfer	BCW66F	$h_{FE}$	75 100 35	160	250	$I_C = 10\text{mA}, V_{CE} = 1\text{V}$ $I_C=100\text{mA}, V_{CE}= 1\text{V}^*$ $I_C=500\text{mA}, V_{CE}= 2\text{V}^*$
	BCW66G	$h_{FE}$	110 160 60	250	400	$I_C = 10\text{mA}, V_{CE} = 1\text{V}$ $I_C=100\text{mA}, V_{CE}= 1\text{V}^*$ $I_C=500\text{mA}, V_{CE}= 2\text{V}^*$
	BCW66H	$h_{FE}$	180 250 100	350	630	$I_C = 10\text{mA}, V_{CE} = 1\text{V}$ $I_C=100\text{mA}, V_{CE}= 1\text{V}^*$ $I_C=500\text{mA}, V_{CE}= 2\text{V}^*$
Transition Frequency	$f_T$	100			MHz	$I_C = 20\text{mA}, V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	$C_{obo}$		8	12	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Input Capacitance	$C_{ibo}$			80	pF	$V_{EB}=0.5\text{V}, f=1\text{MHz}$
Noise Figure	N		2	10	dB	$I_C = 0.2\text{mA}, V_{CE} = 5\text{V}$ $R_G = 1\text{k}\Omega$
Switching times: Turn-On Time Turn-Off Time	$t_{on}$			100	ns	$I_C = 150\text{mA}$
	$t_{off}$			400	ns	$I_{B1} = - I_{B2} = 15\text{mA}$ $R_L = 150\Omega$

Spice parameter data is available upon request for this device

\*Measured under pulsed conditions.